

## Silicon PNP Power Transistors

## 2SA756

**DESCRIPTION**

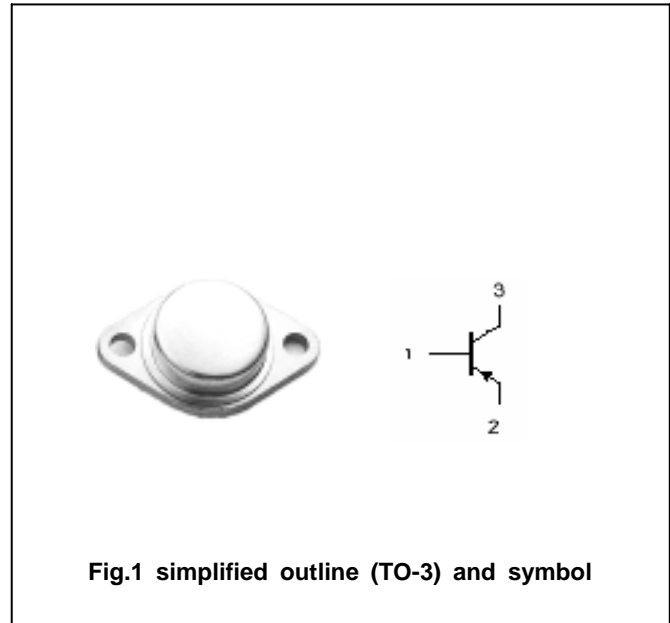
- With TO-3 package
- Complement to type 2SC1030

**APPLICATIONS**

- For audio amplifier power output applications

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta= )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-100	V
$V_{CEO}$	Collector-emitter voltage	Open base	-80	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-6	A
$P_C$	Collector power dissipation	$T_C=25$	50	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA ; R <sub>BE</sub> =	-80			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-5mA , I <sub>E</sub> =0	-100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-5mA , I <sub>C</sub> =0	-6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-1A			-1.8	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-30V; I <sub>E</sub> =0			-1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	35		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-5V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V		20		MHz

◆ h<sub>FE-1</sub> Classifications

A	B	C
35-70	60-120	100-200

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)